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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/617,793	07/14/2003	Yoshiharu Anda	2003_0955A	4076
	03/24/2004		EXAMINER	
WENDEROTH, LIND & PONACK, L.L.P. 2033 K STREET N. W.			PHAM, THANH V	
SUITE 800 WASHINGTON, DC 20006-1021			ART UNIT	PAPER NUMBER
			2823	
			DATE MAILED: 05/24/2004	1

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
Office Action Summers	10/617,793	ANDA ET AL.
Office Action Summary	Examiner	Art Unit
	Thanh V Pham	2823
The MAILING DATE of this communication appeariod for Reply	ears on the cover sheet with the c	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period with Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	6(a). In no event, however, may a reply be tir within the statutory minimum of thirty (30) day ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	mely filed s will be considered timely. the mailing date of this communication.
Status		
1) Responsive to communication(s) filed on 11 Ma	arch 2004.	
2a) ☐ This action is FINAL . 2b) ☒ This	action is non-final.	
3) Since this application is in condition for allowan	ce except for formal matters, pro	osecution as to the ments is
closed in accordance with the practice under Ex		
Disposition of Claims		
4) Claim(s) <u>1-12</u> is/are pending in the application.		
4a) Of the above claim(s) 7-12 is/are withdrawn	from consideration.	•
5) Claim(s) is/are allowed.		;
6)⊠ Claim(s) <u>1-6</u> is/are rejected.		
7) Claim(s) is/are objected to.		•
8) Claim(s) are subject to restriction and/or	election requirement.	
Application Papers		
9) The specification is objected to by the Examiner		
10) The drawing(s) filed on is/are: a) acce	•	•
Applicant may not request that any objection to the d	•	• •
Replacement drawing sheet(s) including the correction		
11)☐ The oath or declaration is objected to by the Exa	iminer. Note the attached Office	Action or form PTO-152.
Priority under 35 U.S.C. § 119		
12)⊠ Acknowledgment is made of a claim for foreign r	oriority under 35 LLS C & 110(a)	(d) or (f)
a)⊠ All b)□ Some * c)□ None of:	onomy under 05 0.0.0. § 115(a)	re(u) or (i).
1.⊠ Certified copies of the priority documents	have been received	
2. Certified copies of the priority documents	•	on No
3. Copies of the certified copies of the priority		
application from the International Bureau		d iii tiiis National Stage
* See the attached detailed Office action for a list o	· •	d
obe the didested detailed office action for a list of	The certified copies not receive	u.
Machine Mark	• • • • • • • • • • • • • • • • • • •	•
Attachment(s)	, e e e e e e e e e e e e e e e e e e e	
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4)	(PTO-413) ite.
Paper No(s)/Mail Date <u>09/15/03</u> .		atent Application (PTO-152)
Patent and Trademark Office		

DETAILED ACTION

Election/Restrictions

1. Applicant's election of Group I, claims 1-6, in Paper filed 03/11/04 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Specification

2. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The following title is suggested: Schottky Junction Electrode Made of Lanthanum Hexaboride.

Drawings

3. Figures 1 and 2 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

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invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

5. Claims 1-6 are rejected under 35 U.S.C. 103(a) as being unpatentable over applicant's admitted prior art in combination with Weitzel et al. US 5,693,969.

Applicant's admitted prior art as in fig. 1 and in pages 2-3 of the specification discloses substantially the same GaAs PHEMT as claimed but lacks the gate electrode made of LaB₆. (The known GaAs PHEMT comprises a Schottky layer 126; and a Schottky electrode 130 that is formed on the Schottky layer and has a Schottky contact with the Schottky layer' wherein the Schottky layer is composed of a compound semiconductor including In and P (InGaP, *re claim 2*), and the portion of the Schottky electrode that touches the Schottky layer is composed of material whose main constituents are not disclosed.)

Re claims 3 and 5, the Weitzel et al. reference discloses a Schottky gate 16 made of LaB₆ (col. 1, line 60 and col. 3, lines 25-27) that helps increasing the breakdown voltage of a FET, does not affect the frequency response, the transconductance and does not require the use of a high resistance refractory gate material (col. 1, lines 15-39). Re claims 4 and 6, the applied "technique is suitable for vertical current flow diodes" (col. 1, line 30) and "to the gate of the MESFET" (col. 1, line 17).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to employ the Schottky gate material of Weitzel et al. as the gate electrode of applicant's admitted prior art because the LaB₆ gate would increase the breakdown voltage of a FET without affecting the frequency response and the

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transconductance, and does not require the use of a high resistance refractory gate

material.

Conclusion

6. The prior art made of record and not relied upon is considered pertinent to

applicant's disclosure.

. 7. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Thanh V. Pham whose telephone number is 571-272-

1866. The examiner can normally be reached on M-T (6:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number

for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the

Patent Application Information Retrieval (PAIR) system. Status information for

published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only.

For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

TvP

05/10/04

Olik Chaudhuri Supervisory Patent Examiner Page 4

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